

General Description

The WSF60N06A uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

Product Summary

BVDSS	RDSON	ID
60V	12mΩ	60A

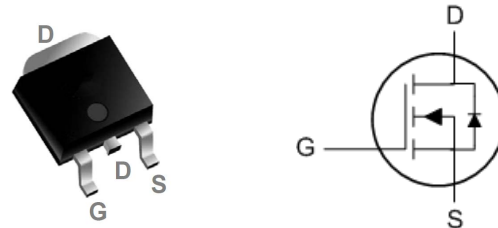
Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- LED backlighting
- Uninterruptible power supply

TO-252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	60	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	41	A
I_{DM}	Pulsed Drain Current ²	120	A
EAS	Single Pulse Avalanche Energy ³	290	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	85	W
T_J, T_{STG}	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.57	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.057	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =30A	---	12	14	mΩ
		V _{GS} =4.5V, I _D =20A	---	15	20	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.68	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =15A	---	30	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	3.4	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =30V, V _{GS} =4.5V, I _D =30A	---	36	45	nC
Q _{gs}	Gate-Source Charge		---	9.9	18	
Q _{gd}	Gate-Drain Charge		---	6.6	15	
T _{d(on)}	Turn-On Delay Time	V _{DS} =30V, V _{GS} =10V, I _D =2A, R=1Ω.	---	12	14.4	ns
T _r	Rise Time		---	5.2	10	
T _{d(off)}	Turn-Off Delay Time		---	38	55	
T _f	Fall Time		---	27	32	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	2498	---	pF
C _{oss}	Output Capacitance		---	185	---	
C _{riss}	Reverse Transfer Capacitance		---	80	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	38	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	90	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =1A, di/dt=100A/μs, T _J =25°C	---	35	---	nS
Q _{rr}	Reverse Recovery Charge		---	47	---	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25

Typical Characteristics

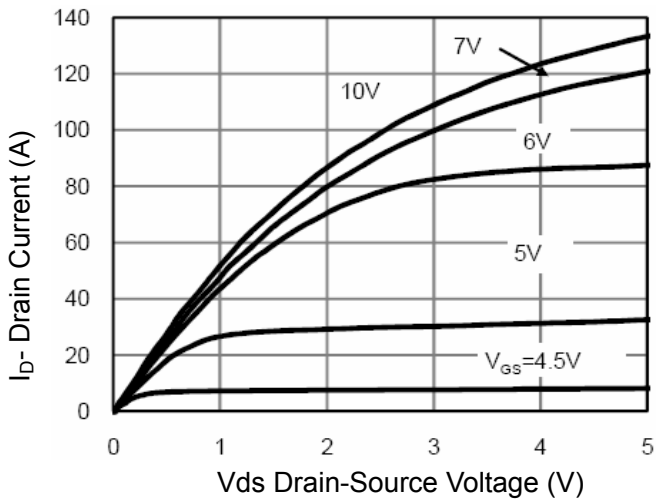


Figure 1 Output Characteristics

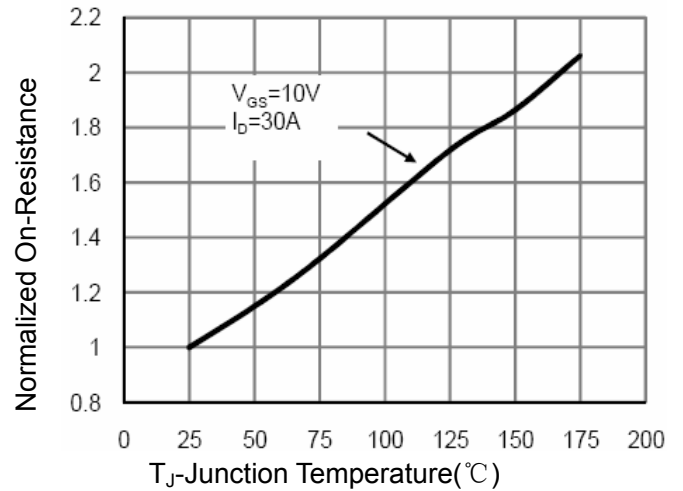


Figure 4 Rdson-Junction Temperature

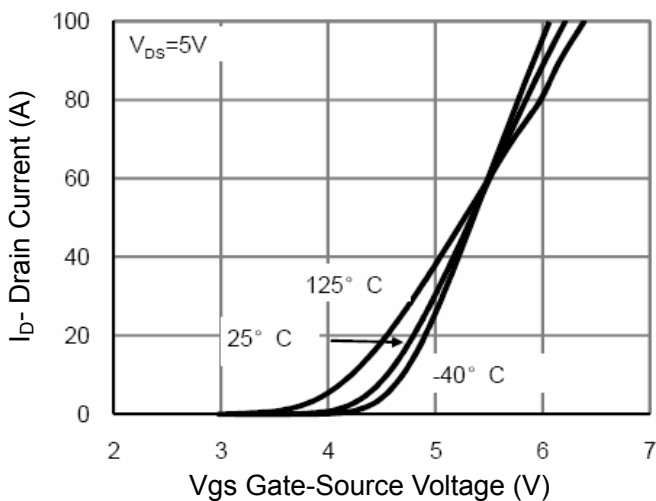


Figure 2 Transfer Characteristics

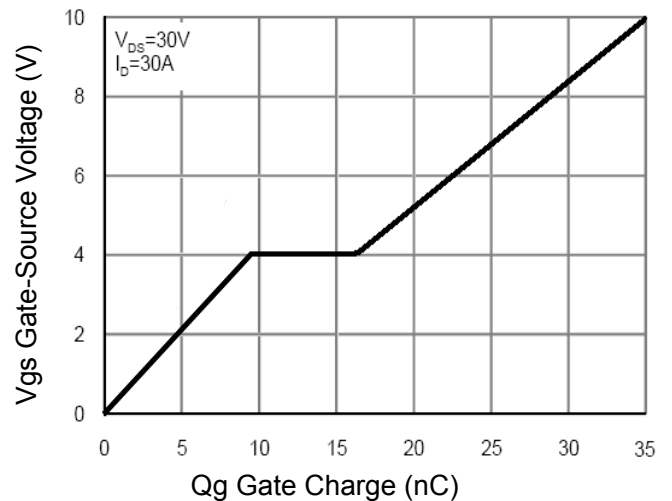


Figure 5 Gate Charge

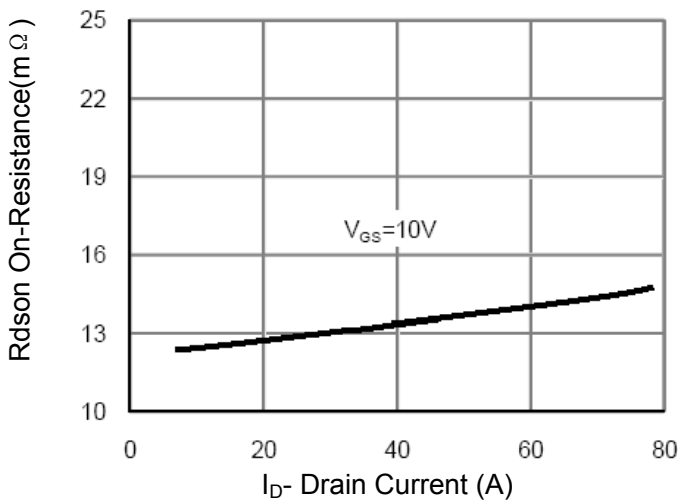


Figure 3 Rdson- Drain Current

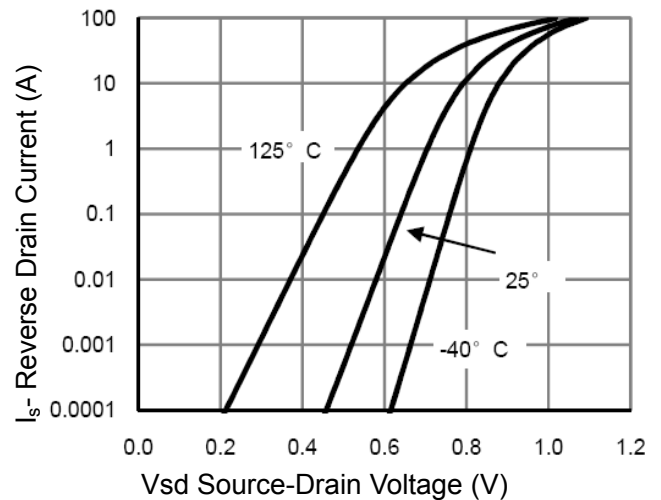


Figure 6 Source- Drain Diode Forward

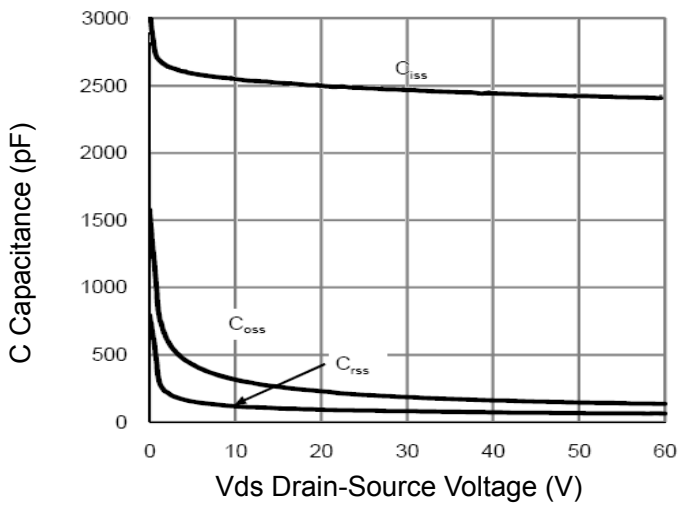


Figure 7 Capacitance vs Vds

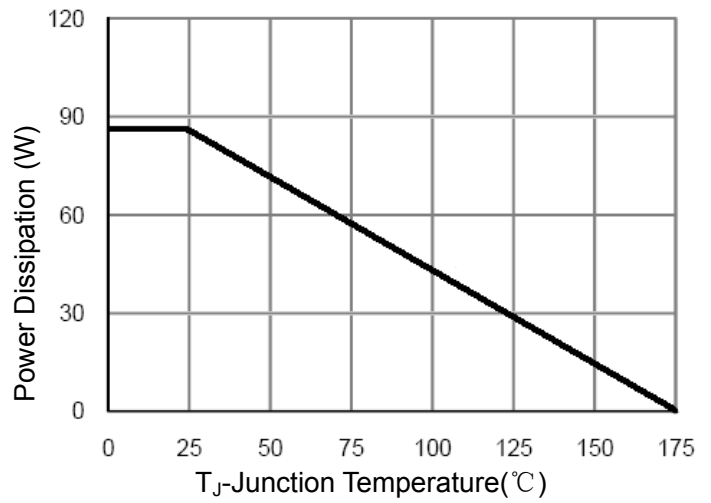


Figure 9 Power De-rating

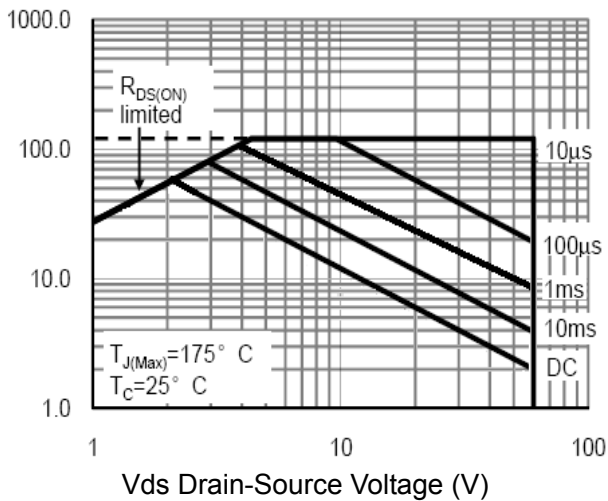


Figure 8 Safe Operation Area

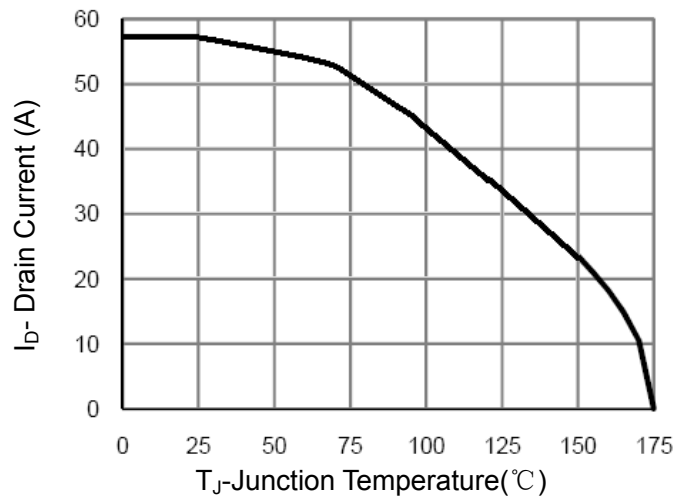


Figure 10 ID Current- Junction Temperature

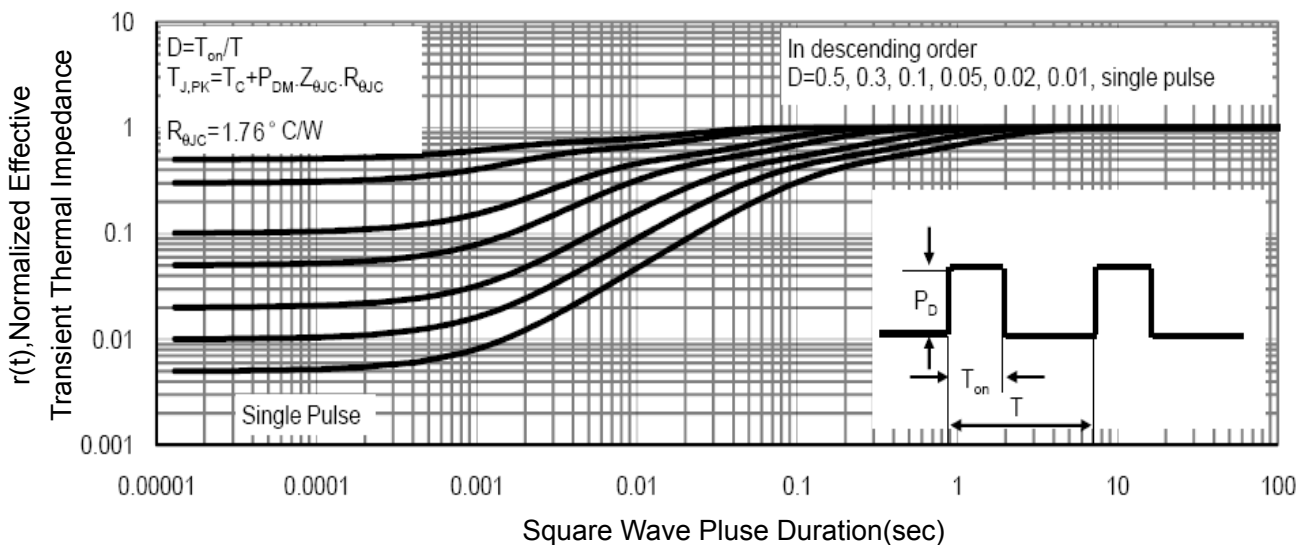


Figure 11 Normalized Maximum Transient Thermal Impedance

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